

**UBSS83**

Preliminary

**POWER MOSFET**

# MOSFET N-CHANNEL ENHANCEMENT SWITCHING TRANSISTOR

## ■ DESCRIPTION

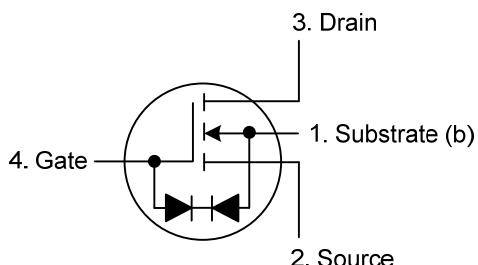
The UTC **UBSS83** is a MOSFET N-channel enhancement switching transistor, it uses UTC's advanced technology to provide customers with a minimum on-state resistance, etc.

The UTC **UBSS83** is suitable for analog and/or digital switch and switch driver.

## ■ FEATURES

- \* Low ON resistance
- \* Low capacitances

## ■ SYMBOL



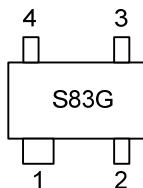
## ■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment				Packing
		1	2	3	4	
UBSS83G-AD4-R	SOT-143	B	S	D	G	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source B: Substrate (b)

UBSS83G-AD4-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AD4: SOT-143 (3) G: Halogen Free and Lead Free
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## ■ MARKING



### ■ ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	10	V
Source-Drain Voltage	$V_{SD}$	10	V
Drain-Substrate Voltage	$V_{DB}$	15	V
Source-Substrate Voltage	$V_{SB}$	15	V
Drain Current (DC)	$I_D$	50	mA
Power Dissipation ( $T_A=25^\circ C$ )	$P_{TOT}$	230	mW
Junction Temperature	$T_J$	125	$^\circ C$
Storage Temperature Range	$T_{STG}$	-65~+150	$^\circ C$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ■ THERMAL RESISTANCE

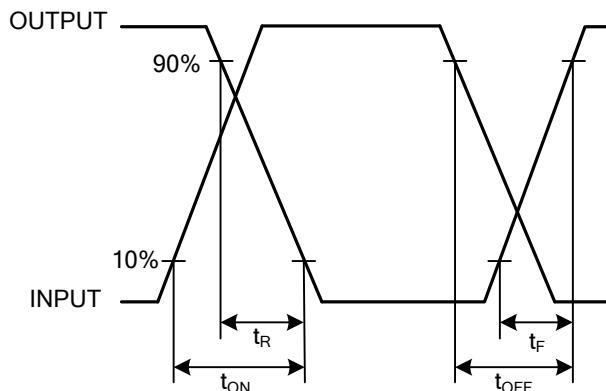
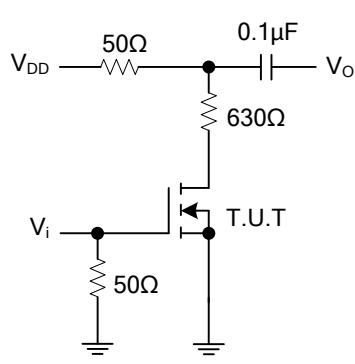
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient in Free Air	$\theta_{JA}$	430	K/W

Note: Device mounted on a ceramic substrate of 8mm×10mm×0.7mm.

### ■ ELECTRICAL CHARACTERISTICS ( $T_{AMB}=25^\circ C$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$BV_{DSX}$	$I_D=10nA, V_{GS}=V_{BS}=-5V$	10			V
Source-Drain Breakdown Voltage	$BV_{SDX}$	$V_{GD}=V_{BD}=-5V, I_D=10nA$	10			V
Drain-Substrate Breakdown Voltage	$BV_{DBO}$	$V_{GB}=0, I_D=10nA$ , Open Source	15			V
Source-Substrate Breakdown Voltage	$BV_{SBO}$	$V_{GB}=0, I_D=10nA$ , Open Drain	15			V
Drain-Source Leakage Current	$I_{DSoff}$	$V_{GS}=V_{BS}=-2V, V_{DS}=6.6V$		10		nA
Source-Drain Leakage Current	$I_{SDoff}$	$V_{GD}=V_{BD}=-2V, V_{SD}=6.6V$		10		nA
Gate-Source Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, V_{SB}=0, I_D=1\mu A$	0.1	2.0		V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=5V, I_D=0.1mA, V_{SB}=0$		70		$\Omega$
		$V_{GS}=10V, I_D=0.1mA, V_{SB}=0$		45		$\Omega$
		$V_{GS}=3.2V, I_D=0.1mA, V_{SB}=6.8V$	80	120		$\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, V_{SB}=0, I_D=20mA, f=1kHz$	10	15		$mS$
Gate-Substrate Zener Voltages	$V_{Z(1)}$	$V_{DB}=V_{SB}=0, -I_G=10\mu A$	12.5			V
	$V_{Z(2)}$	$V_{DB}=V_{SB}=0, +I_G=10\mu A$	12.5			V
Input Capacitance	$C_{iss}$			1.5		pF
Output Capacitance	$C_{oss}$	$V_{GS}=V_{BS}=-15V, V_{DS}=10V, f=1MHz$		1.0		pF
Feed-Back Capacitance	$C_{rss}$			0.6		pF
Switching Times	$t_{ON}$	$V_{DD}=10V, V_i=5V$		1.0		ns
	$t_{OFF}$			5.0		ns

- TEST CIRCUITS AND WAVEFORMS



Switching Times Test Circuit and Input and Output Waveforms.

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